Si Photo Diode Chip--ORT-2155PD

1. Scope：

- The specification applies to NIP silicon photo-diode chips.
- Type：ORT-2155PD

2. Structure：

- NIP planar type.
- Top（Cathode）Side：aluminum(Al) alloy.
- Back（Anode）Side：silver(Ag) alloy.

3. Size：(55mil×55mil)

- Chip size ：(1380μm × 1380μm)± 40μm
- Chip thickness ：280μm ± 20μm
- Active area ：(1220μm × 1220μm) ± 15μm
- Pad size ：(150μm × 150μm)± 10μm
- Pattern drawing：per fig. 1

4. Electro-Optical Characteristics：

(Ta=+25℃)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Forward voltage	V_F	I_F=10mA, H=0	0.5		1.3	V
Reverse Breakdown voltage	V_{BR}	I_R=100μA, H=0	35			V
Reverse Dark Current	I_D	V_R=10V, H=0			10	nA
Light Current	I_L	V_R=5V,Has 1mw/cm^2,@ 940nm		58		μA
Peak Sensing wavelength	λ_P			940		nm

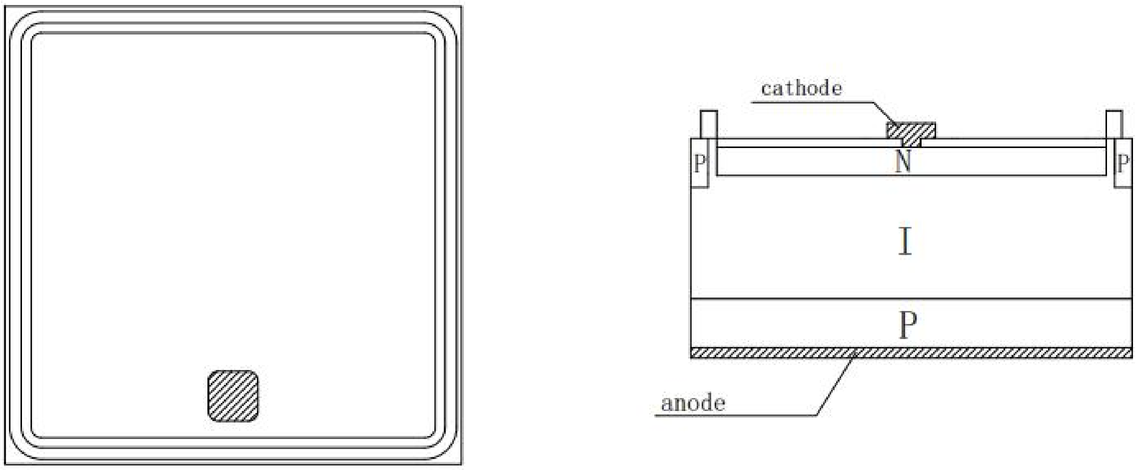

fig.1

5. Spectral Response